

Ordering number : ENA1289



SANYO Semiconductors

DATA SHEET

N-Channel Silicon MOSFET
2SK4203LS — General-Purpose Switching Device
 Applications

Features

- 4V drive.
- Avalanche resistance guarantee.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		45	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		18	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycles≤1%	72	A
Allowable Power Dissipation	P _D		2.0	W
		T _c =25°C	22	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	E _{AS}		28	mJ
Avalanche Current *2	I _{AV}		18	A

Note : *1 V_{DD}=20V, L=100μH, I_{AV}=18A

*2 L≤100μH, Single pulse

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	45			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =45V, V _{GS} =0V			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	1.2		2.6	V

Marking : K4203

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2SK4203LS

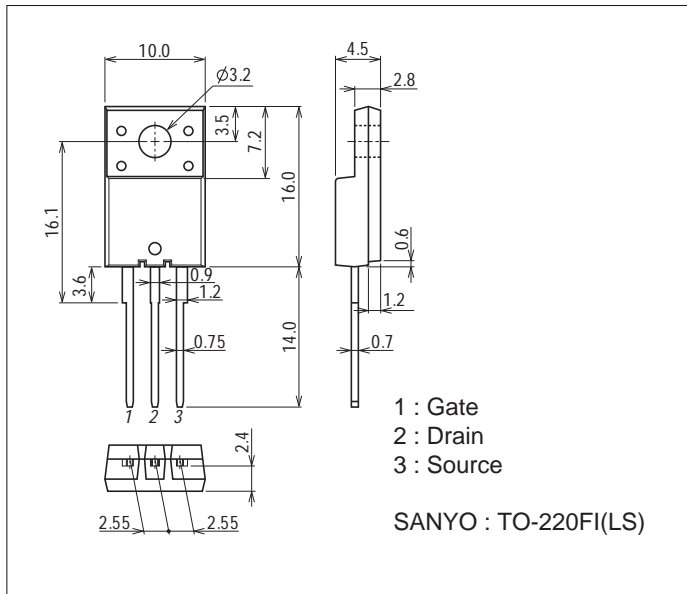
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=9A$	5.4	9.0		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=9A, V_{GS}=10V$		26	34	$m\Omega$
	$R_{DS(on)2}$	$I_D=9A, V_{GS}=4V$		46	64	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS}=20V, f=1MHz$		1020		pF
Output Capacitance	C_{oss}	$V_{DS}=20V, f=1MHz$		140		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=20V, f=1MHz$		100		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		12		ns
Rise Time	t_r	See specified Test Circuit.		71		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		76		ns
Fall Time	t_f	See specified Test Circuit.		59		ns
Total Gate Charge	Q_g	$V_{DS}=24V, V_{GS}=10V, I_D=18A$		21		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=24V, V_{GS}=10V, I_D=18A$		4		nC
Gate-to-Drain "Miller" Charge	Q_{gd}	$V_{DS}=24V, V_{GS}=10V, I_D=18A$		5		nC
Diode Forward Voltage	V_{SD}	$I_S=18A, V_{GS}=0V$		1.0	1.2	V

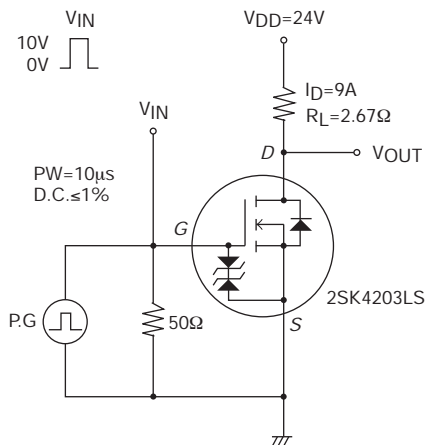
Package Dimensions

unit : mm (typ)

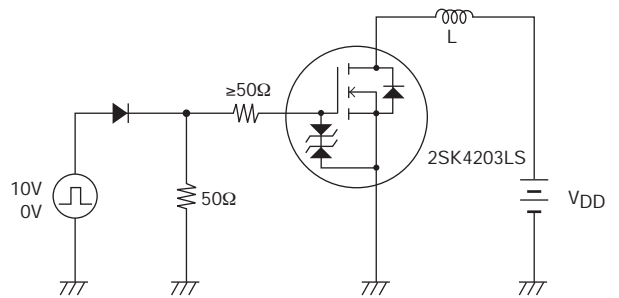
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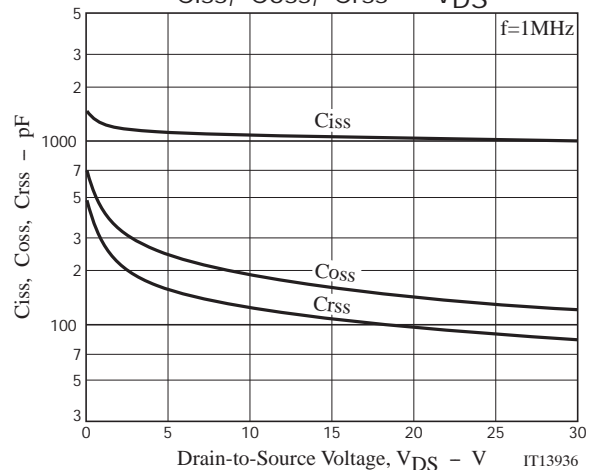
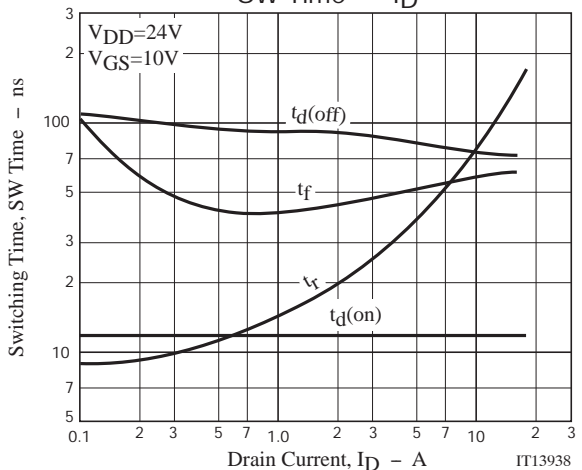
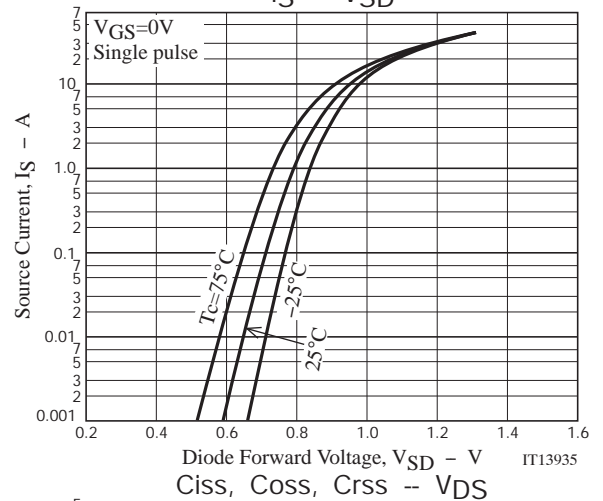
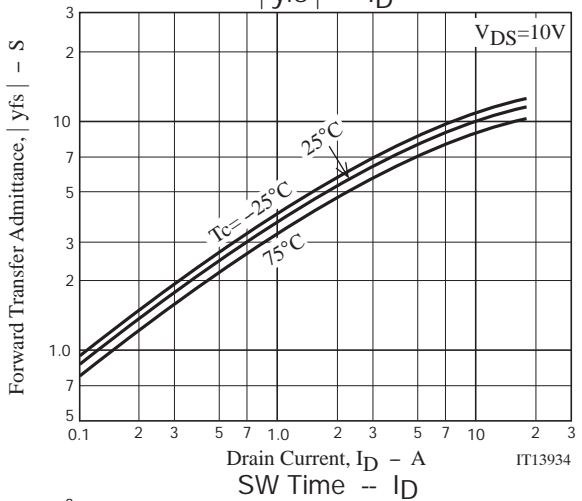
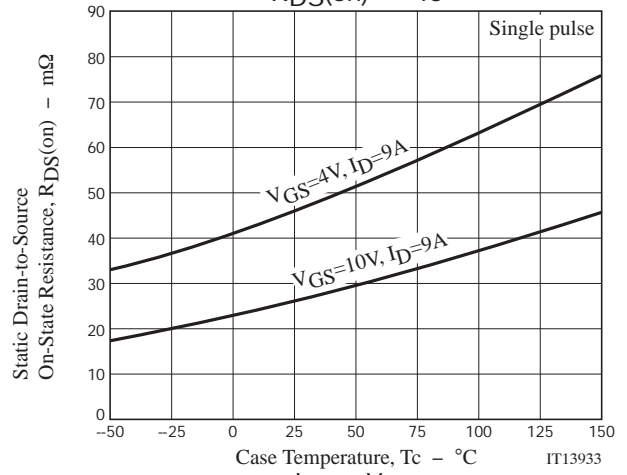
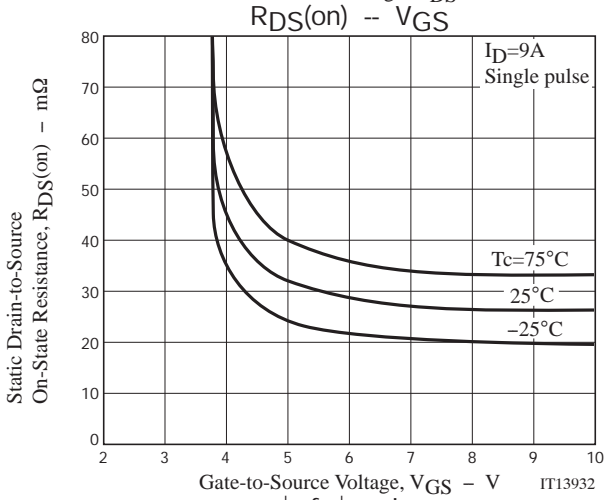
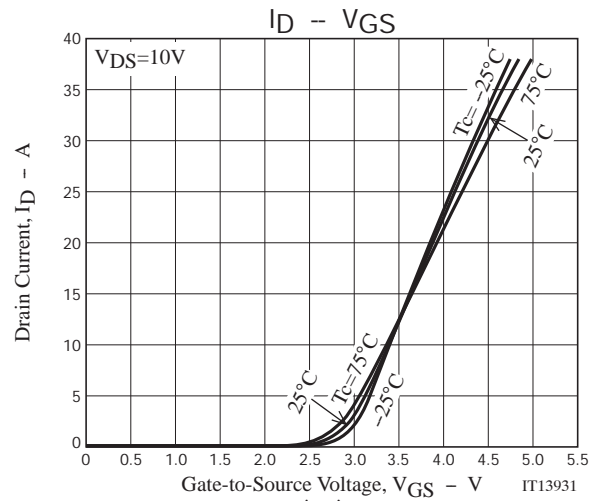
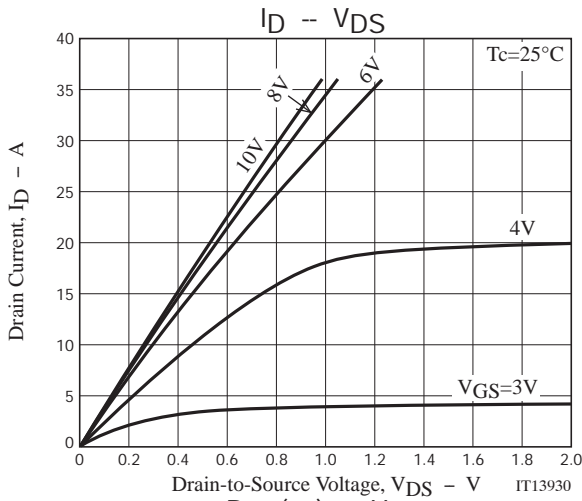
Switching Time Test Circuit



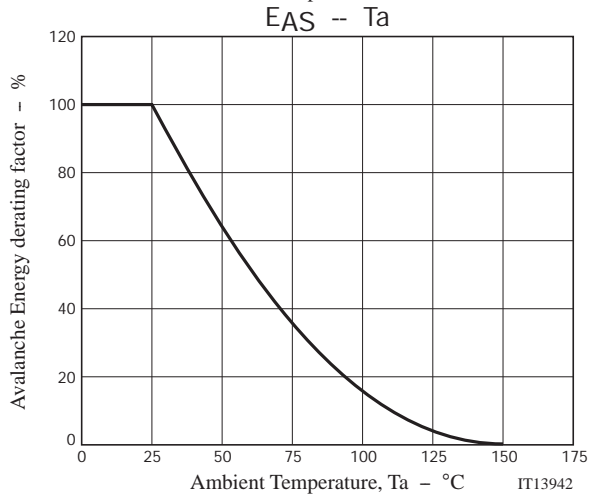
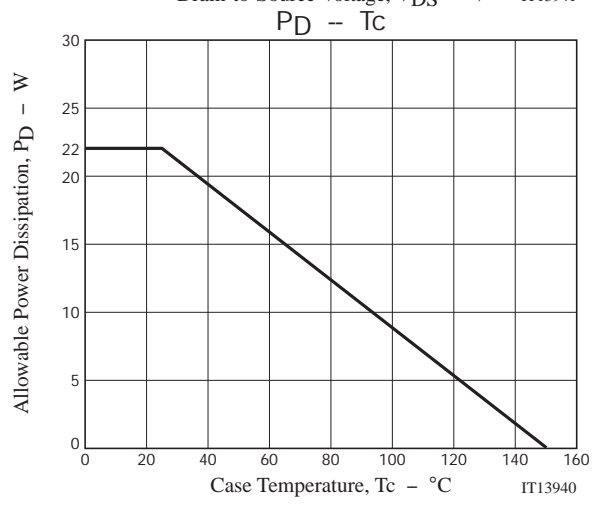
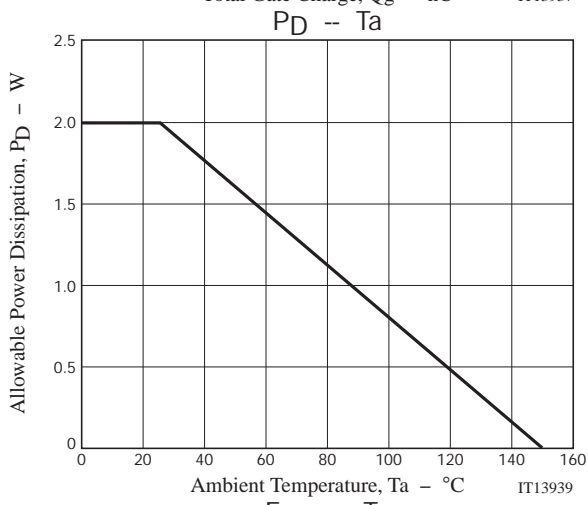
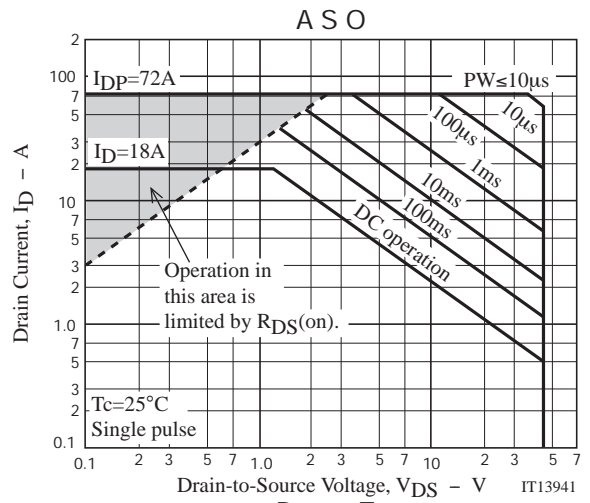
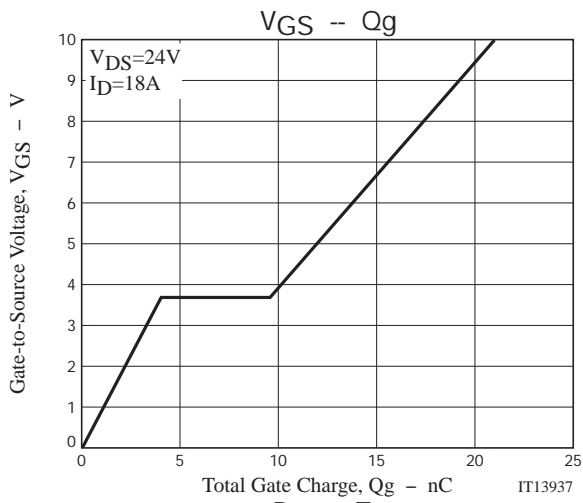
Avalanche Resistance Test Circuit



2SK4203LS



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Note on usage : Since the 2SK4203LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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